

Amend the application identified above as follows:

IN THE CLAIMS

Amend claims 29 and 30 as follows:

~~29.~~ (Once Amended) A method of co-planarizing copper or copper-based metallurgy and a refractory metal-based barrier layer or liner in an interlevel dielectric layer of a semiconductor device comprising the steps of:

planarizing said copper or copper-based metallurgy using a first slurry comprising an oxidizing agent consisting of a metal-based compound, an oxidation inhibitor, a surfactant and an abrasive comprising alumina in water; said first slurry having a pH of between 1.2 and 2.5 and said first slurry for removing copper selectively with respect to said barrier layer or liner;

co-planarizing said barrier layer or liner and said interlevel dielectric layer using a second slurry comprising a peroxide agent, an oxidation inhibitor, a surfactant and an abrasive comprising silica in water; said second slurry having a pH of between 3.0 and 7.5 and said second slurry for removing said barrier layer or liner at a first removal rate and copper at a second removal rate, wherein the first removal rate is greater than the second removal rate.

30. (Once Amended) The method of claim 29 wherein said surfactant in both the first and second slurries comprises a sulfated fatty acid.

Add the following new claims:

31. The method of claim 29, wherein said metal-based compound comprises ferric nitrate.

32. The method of claim 29, wherein the first removal rate is about eight times greater than the second removal rate.

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